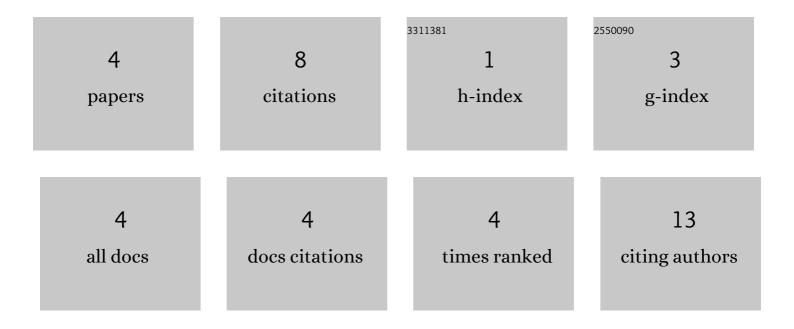
## Hengyu Xu

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/5228485/publications.pdf Version: 2024-02-01



HENCYLL XII

#	Article	IF	CITATIONS
1	Wafer Bonding of SiC-AlN at Room Temperature for All-SiC Capacitive Pressure Sensor. Micromachines, 2019, 10, 635.	2.9	4
2	Influence of curvature induced stress on first principle calculation and the reliability of 4H-SiC (0001) thermally grown SiO2 gate oxide. Microelectronics Reliability, 2019, 100-101, 113317.	1.7	2
3	Effect of pulsed UV laser irradiation on 4H-SiC MOS with thermal gate oxide. Journal of Materials Science: Materials in Electronics, 2020, 31, 5838-5842.	2.2	1
4	Influence of phosphorus diffusion on the SiO2/4H-SiC (0001) interface during poly gate formation process. Microelectronics Reliability, 2021, 126, 114268.	1.7	1